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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

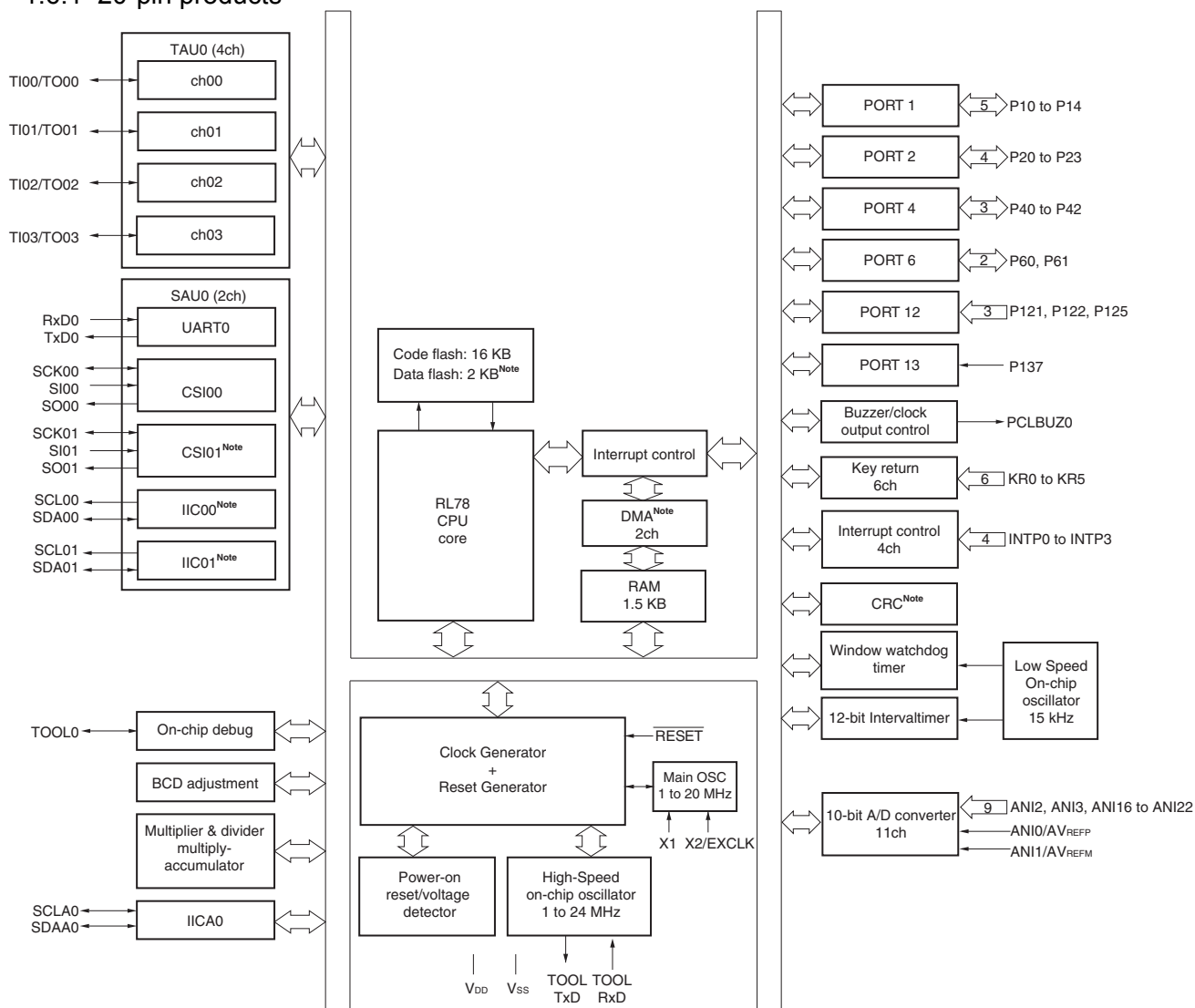
Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	18
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 11x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1027aana-u0

1.6 Block Diagram

1.6.1 20-pin products



Note Provided only in the R5F102 products.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(1/4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	I _{OH1}	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147			–10.0 ^{Note 2}	mA
		20-, 24-pin products: Total of P40 to P42	4.0 V ≤ V _{DD} ≤ 5.5 V		–30.0	mA
			2.7 V ≤ V _{DD} < 4.0 V		–6.0	mA
		30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	1.8 V ≤ V _{DD} < 2.7 V		–4.5	mA
		20-, 24-pin products: Total of P00 to P03 ^{Note 4} , P10 to P14	4.0 V ≤ V _{DD} ≤ 5.5 V		–80.0	mA
			2.7 V ≤ V _{DD} < 4.0 V		–18.0	mA
		30-pin products: Total of P10 to P17, P30, P31, P50, P51, P147 (When duty ≤ 70% ^{Note 3})	1.8 V ≤ V _{DD} < 2.7 V		–10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})			–100	mA
	I _{OH2}	Per pin for P20 to P23			–0.1	mA
		Total of all pins			–0.4	mA

Notes 1. value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = –10.0 mA

$$\text{Total output current of pins} = (-10.0 \times 0.7) / (80 \times 0.01) \cong -8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Caution P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

($T_A = -40$ to $+85^\circ\text{C}$, $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**(4/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, low	V_{OL1}	20-, 24-pin products: P00 to P03 ^{Note} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OL1} = 20.0\text{ mA}$			1.3	V
			$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OL1} = 8.5\text{ mA}$			0.7	V
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OL1} = 3.0\text{ mA}$			0.6	V
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OL1} = 1.5\text{ mA}$			0.4	V
			$1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OL1} = 0.6\text{ mA}$			0.4	V
	V_{OL2}	P20 to P23	$I_{OL2} = 400\text{ }\mu\text{A}$			0.4	V
	V_{OL3}	P60, P61	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OL1} = 15.0\text{ mA}$			2.0	V
			$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OL1} = 5.0\text{ mA}$			0.4	V
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OL1} = 3.0\text{ mA}$			0.4	V
			$1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OL1} = 2.0\text{ mA}$			0.4	V
Input leakage current, high	I_{LIH1}	Other than P121, P122	$V_I = V_{DD}$			1	μA
	I_{LIH2}	P121, P122 (X1, X2/EXCLK)	$V_I = V_{DD}$ Input port or external clock input			1	μA
			When resonator connected			10	μA
Input leakage current, low	I_{LIL1}	Other than P121, P122	$V_I = V_{SS}$			-1	μA
	I_{LIL2}	P121, P122 (X1, X2/EXCLK)	$V_I = V_{SS}$ Input port or external clock input			-1	μA
			When resonator connected			-10	μA
On-chip pull-up resistance	R_U	20-, 24-pin products: P00 to P03 ^{Note} , P10 to P14, P40 to P42, P125, RESET 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	$V_I = V_{SS}$, input port	10	20	100	$\text{k}\Omega$

Note 24-pin products only.**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(3) Peripheral functions (Common to all products)**(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	I _{FIL} ^{Note 1}				0.20		μA
12-bit interval timer operating current	I _{TMKA} ^{Notes 1, 2, 3}				0.02		μA
Watchdog timer operating current	I _{WDT} ^{Notes 1, 2, 4}	f _{IL} = 15 kHz			0.22		μA
A/D converter operating current	I _{ADC} ^{Notes 1, 5}	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.30	1.70	mA
			Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.50	0.70	mA
A/D converter reference voltage operating current	I _{ADREF} ^{Note 1}				75.0		μA
Temperature sensor operating current	I _{TMPS} ^{Note 1}				75.0		μA
LVD operating current	I _{LVD} ^{Notes 1, 6}				0.08		μA
Self-programming operating current	I _{FSP} ^{Notes 1, 8}				2.00	12.20	mA
BGO operating current	I _{BGO} ^{Notes 1, 7}				2.00	12.20	mA
SNOOZE operating current	I _{SNOZ} ^{Note 1}	ADC operation	The mode is performed ^{Note 9}		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		1.20	1.44	mA
		CSI/UART operation			0.70	0.84	mA

Notes 1. Current flowing to the V_{DD}.

2. When high speed on-chip oscillator and high-speed system clock are stopped.

3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3}, and I_{FIL} and I_{TMKA} when the 12-bit interval timer operates.4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates.5. Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.6. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit operates.

7. Current flowing only during data flash rewrite.

8. Current flowing only during self programming.

9. For shift time to the SNOOZE mode, see **17.3.3 SNOOZE mode**.**Remarks** 1. f_{IL}: Low-speed on-chip oscillator clock frequency2. Temperature condition of the TYP. value is T_A = 25°C

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)**(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK}	2.7 V ≤ V _{DD} ≤ 5.5 V	167		500		ns
			2.4 V ≤ V _{DD} ≤ 5.5 V	250		500		ns
			1.8 V ≤ V _{DD} ≤ 5.5 V	—		500		ns
SCKp high-/low-level width	t _{KH1} , t _{KL1}	4.0 V ≤ V _{DD} ≤ 5.5 V		t _{KCY1} /2–12		t _{KCY1} /2–50		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V		t _{KCY1} /2–18		t _{KCY1} /2–50		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		t _{KCY1} /2–38		t _{KCY1} /2–50		ns
		1.8 V ≤ V _{DD} ≤ 5.5 V		—		t _{KCY1} /2–50		ns
Slp setup time (to SCKp↑) <small>Note 1</small>	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V		44		110		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V		44		110		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		75		110		ns
		1.8 V ≤ V _{DD} ≤ 5.5 V		—		110		ns
Slp hold time (from SCKp↑) <small>Note 2</small>	t _{SH1}			19		19		ns
Delay time from SCKp↓ to SOp output <small>Note 3</small>	t _{KSO1}	C = 30 pF <small>Note 4</small>			25		25	ns

- Notes**
1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

- Remarks**
1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: “1, 3” is only for the R5F102 products)
 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: “1, 3” is only for the R5F102 products.))

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

 $(T_A = -40$ to $+85^\circ\text{C}$, $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	200		1150		ns
			$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	300		1150		ns
SCK00 high-level width	t_{KH1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		$t_{KCY1}/2 - 50$		$t_{KCY1}/2 - 50$		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		$t_{KCY1}/2 - 120$		$t_{KCY1}/2 - 120$		ns
SCK00 low-level width	t_{KL1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		$t_{KCY1}/2 - 7$		$t_{KCY1}/2 - 50$		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		$t_{KCY1}/2 - 10$		$t_{KCY1}/2 - 50$		ns
SI00 setup time (to SCK00 \uparrow) ^{Note 1}	t_{SIK1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		58		479		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		121		479		ns
SI00 hold time (from SCK00 \uparrow) ^{Note 1}	t_{KSI1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		10		10		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		10		10		ns
Delay time from SCK00 \downarrow to SO00 output ^{Note 1}	t_{KSO1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$			60		60	ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$			130		130	ns
SI00 setup time (to SCK00 \downarrow) ^{Note 2}	t_{SIK1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		23		110		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		33		110		ns
SI00 hold time (from SCK00 \downarrow) ^{Note 2}	t_{KSI1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		10		10		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		10		10		ns
Delay time from SCK00 \uparrow to SO00 output ^{Note 2}	t_{KSO1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 1.4\text{ k}\Omega$			10		10	ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 20\text{ pF}$, $R_b = 2.7\text{ k}\Omega$			10		10	ns

(Notes, Caution, and Remarks are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)**($T_A = -40$ to $+85^\circ\text{C}$, $1.8\text{ V} \leq V_{DD} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	300		1150		ns
			$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	500		1150		ns
			$1.8\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}^{\text{Note}}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	1150		1150		ns
SCKp high-level width	t_{KH1}		$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	$t_{KCY1}/2 - 75$		$t_{KCY1}/2 - 75$		ns
			$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$t_{KCY1}/2 - 170$		$t_{KCY1}/2 - 170$		ns
			$1.8\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}^{\text{Note}}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	$t_{KCY1}/2 - 458$		$t_{KCY1}/2 - 458$		ns
SCKp low-level width	t_{KL1}		$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	$t_{KCY1}/2 - 12$		$t_{KCY1}/2 - 50$		ns
			$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$t_{KCY1}/2 - 18$		$t_{KCY1}/2 - 50$		ns
			$1.8\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}^{\text{Note}}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	$t_{KCY1}/2 - 50$		$t_{KCY1}/2 - 50$		ns

Note Use it with $V_{DD} \geq V_b$.

Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

Remarks 1. R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage

2. p: CSI number (p = 00, 20)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)
(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 1}	t _{KCY2}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	20 MHz < f _{MCK} ≤ 24 MHz	12/f _{MCK}		—		ns
			8 MHz < f _{MCK} ≤ 20 MHz	10/f _{MCK}		—		ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/f _{MCK}		16/f _{MCK}		ns
			f _{MCK} ≤ 4 MHz	6/f _{MCK}		10/f _{MCK}		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	20 MHz < f _{MCK} ≤ 24 MHz	16/f _{MCK}		—		ns
			16 MHz < f _{MCK} ≤ 20 MHz	14/f _{MCK}		—		ns
			8 MHz < f _{MCK} ≤ 16 MHz	12/f _{MCK}		—		ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/f _{MCK}		16/f _{MCK}		ns
			f _{MCK} ≤ 4 MHz	6/f _{MCK}		10/f _{MCK}		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	20 MHz < f _{MCK} ≤ 24 MHz	36/f _{MCK}		—		ns
			16 MHz < f _{MCK} ≤ 20 MHz	32/f _{MCK}		—		ns
			8 MHz < f _{MCK} ≤ 16 MHz	26/f _{MCK}		—		ns
			4 MHz < f _{MCK} ≤ 8 MHz	16/f _{MCK}		16/f _{MCK}		ns
			f _{MCK} ≤ 4 MHz	10/f _{MCK}		10/f _{MCK}		ns
SCKp high-/low-level width	t _{KH2} , t _{KL2}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V		t _{KCY2} /2 - 12		t _{KCY2} /2 - 50		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V		t _{KCY2} /2 - 18		t _{KCY2} /2 - 50		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}		t _{KCY2} /2 - 50		t _{KCY2} /2 - 50		ns
Slp setup time (to SCKp↑) ^{Note 3}	t _{SIK2}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _{DD} ≤ 4.0 V		1/f _{MCK} + 20		1/f _{MCK} + 30		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V		1/f _{MCK} + 20		1/f _{MCK} + 30		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _{DD} ≤ 2.0 V ^{Note 2}		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
Slp hold time (from SCKp↑) ^{Note 4}	t _{KSI2}			1/f _{MCK} + 31		1/f _{MCK} + 31		ns
Delay time from SCKp↓ to SOP output ^{Note 5}	t _{KSO2}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ			2/f _{MCK} + 120		2/f _{MCK} + 573	ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ			2/f _{MCK} + 214		2/f _{MCK} + 573	ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ			2/f _{MCK} + 573		2/f _{MCK} + 573	ns

- Notes**
1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 2. Use it with V_{DD} ≥ V_b.
 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOP output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Cautions

1. Select the TTL input buffer for the Slp and SCKp pins and the N-ch open drain output (V_{DD} tolerance) mode for the SOP pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).
For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (-) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (-) = AV_{REFM}
ANI0 to ANI3	Refer to 28.6.1 (1).	Refer to 28.6.1 (3).	Refer to 28.6.1 (4).
ANI16 to ANI22	Refer to 28.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 28.6.1 (1).		—

(1) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (-) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+85^\circ\text{C}$, $1.8\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			1.2	± 3.5	LSB
					1.2	± 7.0 ^{Note 4}	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2, ANI3	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
				57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 0.25	%FSR
						± 0.50 ^{Note 4}	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 0.25	%FSR
						± 0.50 ^{Note 4}	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 2.5	LSB
						± 5.0 ^{Note 4}	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 1.5	LSB
						± 2.0 ^{Note 4}	LSB
Analog input voltage	V_{AIN}	ANI2, ANI3		0		AV_{REFP}	V
		Internal reference voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{BGR} ^{Note 5}			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{TMPS25} ^{Note 5}			V

(Notes are listed on the next page.)

2.6.2 Temperature sensor/internal reference voltage characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, HS (high-speed main) mode)

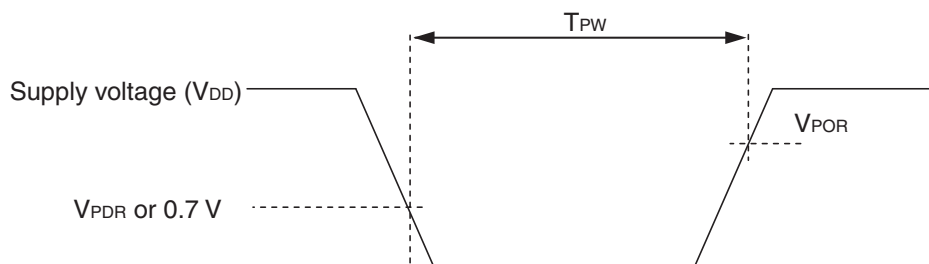
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, $T_A = +25^\circ\text{C}$		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	F_{VTMPS}	Temperature sensor output voltage that depends on the temperature		-3.6		mV/ $^\circ\text{C}$
Operation stabilization wait time	t_{AMP}		5			μs

2.6.3 POR circuit characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.47	1.51	1.55	V
	V_{PDR}	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR} . This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



LVD detection voltage of interrupt & reset mode**($T_A = -40$ to $+85^\circ\text{C}$, $V_{PDR} \leq V_{DD} \leq 5.5$ V, $V_{SS} = 0$ V)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V _{LVD0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 1, falling reset voltage		1.80	1.84	1.87	V
	V _{LVD1}	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V
	V _{LVD2}	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	V _{LVD3}	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	V _{LVD0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 0, falling reset voltage		2.40	2.45	2.50	V
	V _{LVD1}	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	V _{LVD2}	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	V _{LVD3}	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.68	3.75	3.82	V
			Falling interrupt voltage	3.60	3.67	3.74	V
	V _{LVD0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 1, falling reset voltage		2.70	2.75	2.81	V
	V _{LVD1}	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	V _{LVD2}	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V
	V _{LVD3}	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.98	4.06	4.14	V
			Falling interrupt voltage	3.90	3.98	4.06	V

2.6.5 Power supply voltage rising slope characteristics**($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0$ V)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S _{VDD}				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 28.4 AC Characteristics.

(1) 20-, 24-pin products

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current ^{Note 1}	I _{DD2} ^{Note 2}	HALT mode	HS (High-speed main) mode ^{Note 6}	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	2230	μA
					V _{DD} = 3.0 V		440	2230	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1650	μA
					V _{DD} = 3.0 V		400	1650	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		190	1010	μA
					Resonator connection		260	1090	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		190	1010	μA
					Resonator connection		260	1090	
	I _{DD3} ^{Note 5}	STOP mode	T _A = -40°C				0.19	0.50	μA
			T _A = +25°C				0.24	0.50	
			T _A = +50°C				0.32	0.80	
			T _A = +70°C				0.48	1.20	
			T _A = +85°C				0.74	2.20	
			T _A = +105°C				1.50	10.20	

- Notes**
1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator clock is stopped.
 4. When high-speed system clock is stopped.
 5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

- Remarks**
1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH}: high-speed on-chip oscillator clock frequency
 3. Except temperature condition of the TYP. value is T_A = 25°C, other than STOP mode

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	334	ns
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	500	ns
SCKp high-/low-level width	t_{KH1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	$t_{KCY1}/2-24$		ns
	t_{KL1}	$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	$t_{KCY1}/2-36$		ns
		$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	$t_{KCY1}/2-76$		ns
Slp setup time (to SCKp \uparrow) ^{Note 1}	t_{SIK1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	66		ns
		$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	66		ns
		$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	113		ns
Slp hold time (from SCKp \uparrow) ^{Note 2}	t_{KSI1}		38		ns
Delay time from SCKp \downarrow to SOp output ^{Note 3}	t_{KSO1}	$C = 30\text{ pF}$ ^{Note 4}		50	ns

- Notes**
1. When $DAPmn = 0$ and $CKPmn = 0$, or $DAPmn = 1$ and $CKPmn = 1$. The Slp setup time becomes “to SCKp \downarrow ” when $DAPmn = 0$ and $CKPmn = 1$, or $DAPmn = 1$ and $CKPmn = 0$.
 2. When $DAPmn = 0$ and $CKPmn = 0$, or $DAPmn = 1$ and $CKPmn = 1$. The Slp hold time becomes “from SCKp \downarrow ” when $DAPmn = 0$ and $CKPmn = 1$, or $DAPmn = 1$ and $CKPmn = 0$.
 3. When $DAPmn = 0$ and $CKPmn = 0$, or $DAPmn = 1$ and $CKPmn = 1$. The delay time to SOp output becomes “from SCKp \uparrow ” when $DAPmn = 0$ and $CKPmn = 1$, or $DAPmn = 1$ and $CKPmn = 0$.
 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

- Remarks**
1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)
 2. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3))

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
5. The smaller maximum transfer rate derived by using f_{MCK}/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \quad [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

6. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.
7. The smaller maximum transfer rate derived by using f_{MCK}/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V

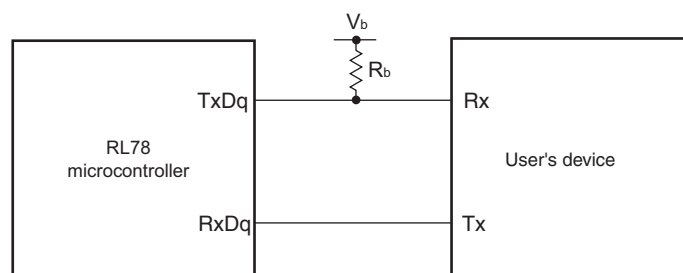
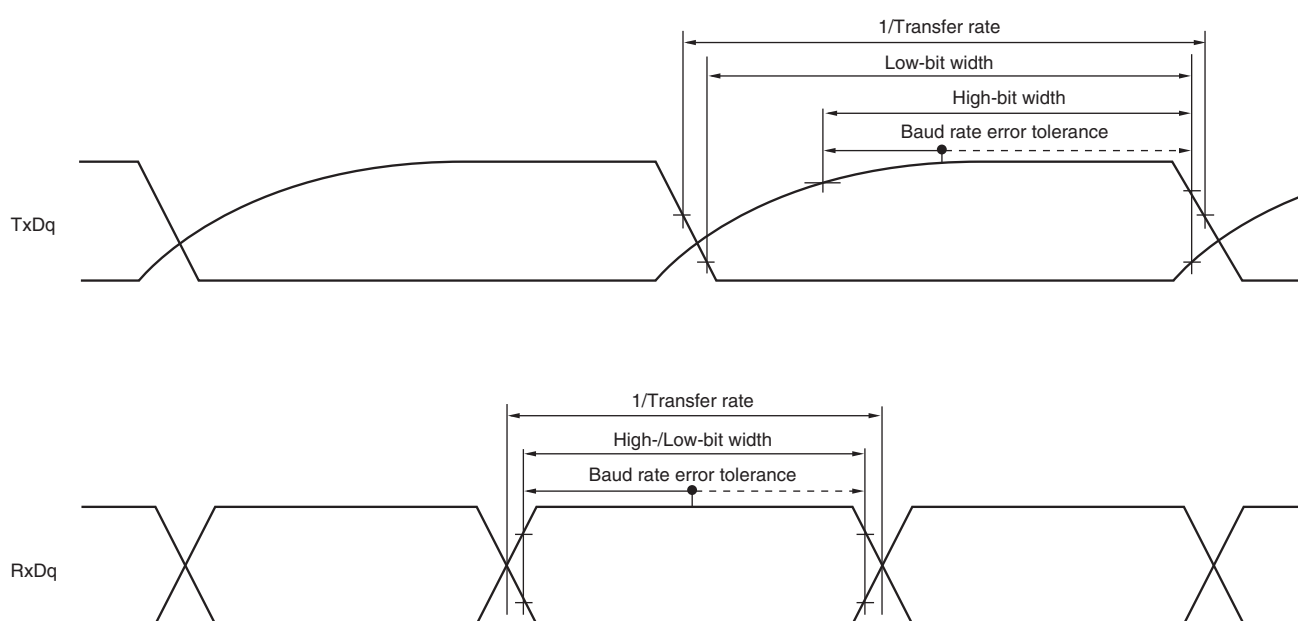
$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \quad [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

8. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 7** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). **For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

UART mode connection diagram (during communication at different potential)**UART mode bit width (during communication at different potential) (reference)**

- Remarks**
1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $C_b[\text{F}]$: Communication line (TxDq) load capacitance, $V_b[\text{V}]$: Communication line voltage
 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))
 4. UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	600		ns
			$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1000		ns
			$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	2300		ns
SCKp high-level width	t_{KH1}		$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	$t_{KCY1}/2 - 150$		ns
			$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$t_{KCY1}/2 - 340$		ns
			$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	$t_{KCY1}/2 - 916$		ns
SCKp low-level width	t_{KL1}		$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	$t_{KCY1}/2 - 24$		ns
			$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$t_{KCY1}/2 - 36$		ns
			$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	$t_{KCY1}/2 - 100$		ns

- Cautions**
1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.
 2. CSI01 and CSI11 cannot communicate at different potential.

- Remarks**
1. R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage
 2. p: CSI number (p = 00, 20)

3.5.2 Serial interface IICA

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) mode				Unit
			Standard Mode		Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode: f _{CLK} ≥ 3.5 MHz			0	400	kHz
		Normal mode: f _{CLK} ≥ 1 MHz	0	100			kHz
Setup time of restart condition	t _{SU:STA}		4.7		0.6		μs
Hold time ^{Note 1}	t _{HD:STA}		4.0		0.6		μs
Hold time when SCLA0 = “L”	t _{LOW}		4.7		1.3		μs
Hold time when SCLA0 = “H”	t _{HIGH}		4.0		0.6		μs
Data setup time (reception)	t _{SU:DAT}		250		100		ns
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}		0	3.45	0	0.9	μs
Setup time of stop condition	t _{SU:STO}		4.0		0.6		μs
Bus-free time	t _{BUF}		4.7		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

<R> 2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

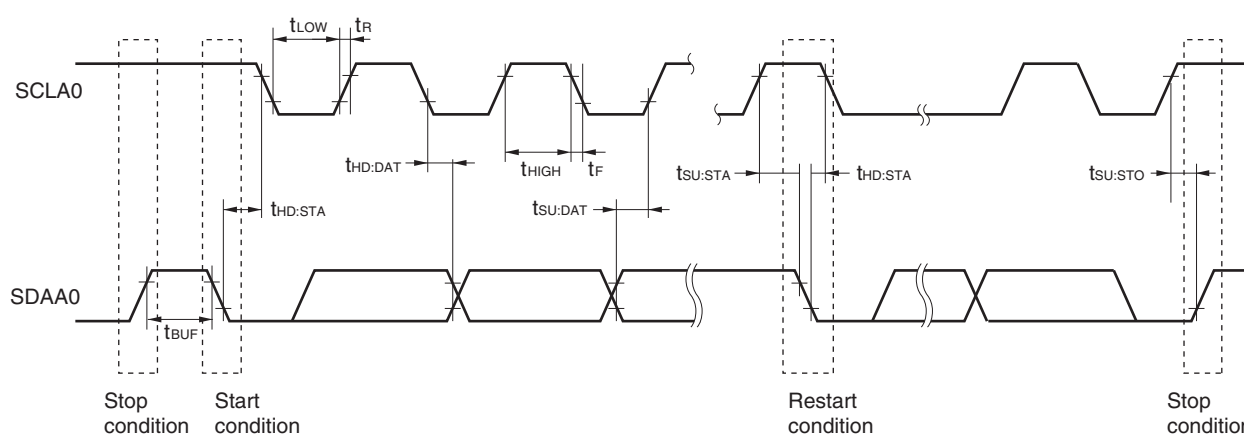
Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1} , I_{OL1} , V_{OH1} , V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Normal mode: $C_b = 400\text{ pF}$, $R_b = 2.7\text{ k}\Omega$

Fast mode: $C_b = 320\text{ pF}$, $R_b = 1.1\text{ k}\Omega$

IICA serial transfer timing



LVD detection voltage of interrupt & reset mode**($T_A = -40$ to $+105^\circ\text{C}$, $V_{PDR} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V _{LVDD0}	V _{POC2} , V _{POC1} , V _{POC1} = 0, 1, 1, falling reset voltage		2.64	2.75	2.86	V
	V _{LVDD1}	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.81	2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	V _{LVDD2}	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	V _{LVDD3}	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

3.6.5 Power supply voltage rising slope characteristics**($T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S _{VDD}				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 29.4 AC Characteristics.

Revision History	RL78/G12 Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Dec 10, 2012	-	First Edition issued
2.00	Sep 06, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4	Modification of Table 1-1. List of Ordering Part Numbers, Note, and Caution
		7 to 9	Modification of package name in 1.4.1 to 1.4.3
		14	Modification of tables in 1.7 Outline of Functions
		17	Modification of description of table in 2.1 Absolute Maximum Ratings (TA = 25°C)
		18	Modification of table, Note, and Caution in 2.2.1 X1 oscillator characteristics
		18	Modification of table in 2.2.2 On-chip oscillator characteristics
		19	Modification of Note 3 in 2.3.1 Pin characteristics (1/4)
		20	Modification of Note 3 in 2.3.1 Pin characteristics (2/4)
		23	Modification of Notes 1 and 2 in (1) 20-, 24-pin products (1/2)
		24	Modification of Notes 1 and 3 in (1) 20-, 24-pin products (2/2)
		25	Modification of Notes 1 and 2 in (2) 30-pin products (1/2)
		26	Modification of Notes 1 and 3 in (2) 30-pin products (2/2)
		27	Modification of (3) Peripheral functions (Common to all products)
		28	Modification of table in 2.4 AC Characteristics
		29	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		30	Modification of figures of AC Timing Test Point and External Main System Clock Timing
		31	Modification of figure of AC Timing Test Point
		31	Modification of description and Note 2 in (1) During communication at same potential (UART mode)
		32	Modification of description in (2) During communication at same potential (CSI mode)
		33	Modification of description in (3) During communication at same potential (CSI mode)
		34	Modification of description in (4) During communication at same potential (CSI mode)
		36	Modification of table and Note 2 in (5) During communication at same potential (simplified I ² C mode)
		38, 39	Modification of table and Notes 1 to 9 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)
		40	Modification of Remarks 1 to 3 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)
		41	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode)
		42	Modification of Caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode)
		43	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		44	Modification of table and Notes 1 and 2 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		45	Modification of table, Note 1, and Caution 1 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		47	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)
		50	Modification of table, Note 1, and Caution 1 in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode)
		52	Modification of Remark in 2.5.2 Serial interface IICA
		53	Addition of table to 2.6.1 A/D converter characteristics
		53	Modification of description in 2.6.1 (1)
		54	Modification of Notes 3 to 5 in 2.6.1 (1)
		54	Modification of description and Notes 2 to 4 in 2.6.1 (2)

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